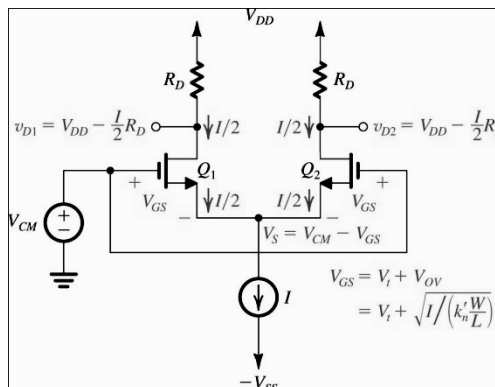


Homework #4

1. For the MOS differential pair with a common-mode voltage V_{CM} applied, as shown below, let $V_{DD}=V_{SS}=1.5V$, $k_n'(W/L)=4mA/V^2$, $V_t=0.5V$, $I=0.4mA$, and $R_D=2.5k\Omega$ (neglect channel-length modulation). Assume that the current source I requires a minimum voltage of $0.4V$ to operate properly. (worth 2 problems)

- Find V_{GS} for each transistor.
- For $V_{CM}=0$ find V_S , I_{D1} , I_{D2} , V_{D1} , and V_{D2} .
- Repeat (b) for $V_{CM}=1V$.
- Repeat (b) for $V_{CM}=-0.2V$.
- What is the highest permitted value of V_{CM} ?
- What is the lowest value of V_{CM} ?



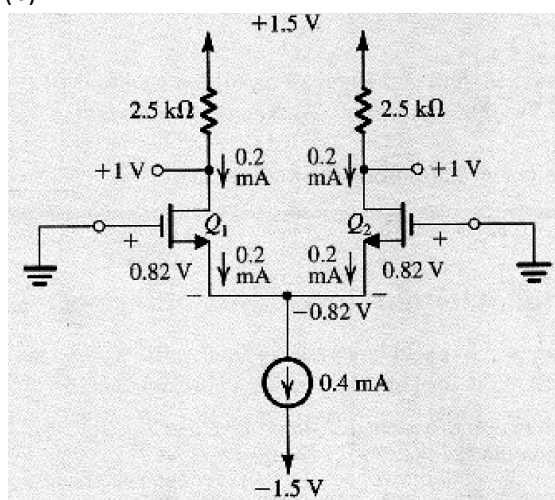
(a) $v_{G1} = v_{G2} = V_{CM}$

$$I_{D1} = I_{D2} = \frac{I}{2} = \frac{1}{2} k_n' (W/L) V_{OV}^2 \quad \text{where } V_{OV} = (V_{GS} - V_t)$$

$$\frac{0.4}{2} = \frac{1}{2} \times 4 V_{OV}^2 \Rightarrow V_{OV} = 0.316 \text{ V}$$

$$V_{GS} = V_t + V_{OV} = 0.5 + 0.316 \approx 0.82 \text{ V}$$

(b)

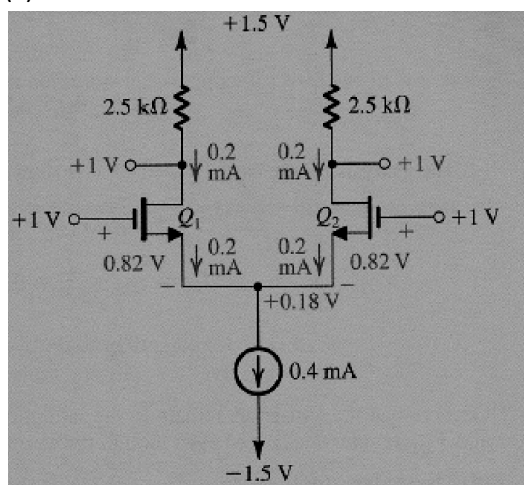


$$V_S = V_G - V_{GS} = 0 - 0.82 = -0.82 \text{ V}$$

$$I_{D1} = I_{D2} = \frac{I}{2} = 0.2 \text{ mA}$$

$$V_{D1} = V_{D2} = V_{DD} - \frac{I}{2} R_D = 1.5 - 0.2 \times 2.5 = 1 \text{ V}$$

(c)



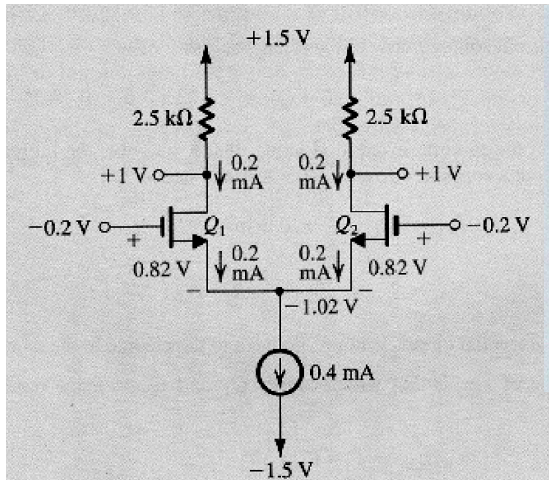
$$V_S = V_G - V_{GS} = 1 - 0.82 = +0.18 \text{ V}$$

$$I_{D1} = I_{D2} = \frac{I}{2} = 0.2 \text{ mA}$$

$$V_{D1} = V_{D2} = V_{DD} - \frac{I}{2} R_D = 1.5 - 0.2 \times 2.5 = +1 \text{ V}$$

Observe that the transistors remain in the saturation region as assumed. Also observe that I_{D1} , I_{D2} , V_{D1} , and V_{D2} remain unchanged even though the common-mode voltage V_{CM} changed by 1 V.

(d)



$$V_S = V_G - V_{GS} = -0.2 - 0.82 = -1.02 \text{ V}$$

It follows that the current source I now has a voltage across it of

$$V_{CS} = -V_S - (-V_{SS}) = -1.02 + 1.5 = 0.48 \text{ V}$$

which is greater than the minimum required value of 0.4 V. Thus, the current source is still operating properly and delivering a constant current $I = 0.4 \text{ mA}$ and hence

$$I_{D1} = I_{D2} = \frac{I}{2} = 0.2 \text{ mA}$$

$$V_{D1} = V_{D2} = V_{DD} - \frac{I}{2} R_D = +1 \text{ V}$$

So, here again the differential circuit is not responsive to the change in the common-mode voltage V_{CM} .

(e) The highest value of V_{CM} is that which causes Q_1 and Q_2 to leave saturation and enter the triode region. Thus,

$$\begin{aligned} V_{CM_{\max}} &= V_t + V_D \\ &= 0.5 + 1 = +1.5 \text{ V} \end{aligned}$$

(f) The lowest value allowed for V_{CM} is that which reduces the voltage across the current source I to the minimum required of $V_{CS} = 0.4 \text{ V}$. Thus,

$$\begin{aligned} V_{CM_{\min}} &= -V_{SS} + V_{CS} + V_{GS} \\ &= -1.5 + 0.4 + 0.82 = -0.28 \text{ V} \end{aligned}$$

Thus, the input common-mode range is

$$-0.28 \text{ V} \leq V_{CM} \leq +1.5 \text{ V}$$

2. For the amplifier of Problem 1, find the input common-mode range for the case in which the two drain resistances R_D are increased by a factor of 2.

If R_D is doubled to 5 K,

$$\begin{aligned} V_{D1} &= V_{D2} = V_{DD} - \frac{I}{2} R_D \\ &= 1.5 - \frac{0.4 \text{ mA}}{2} (5 \text{ K}) = 0.5 \text{ V} \end{aligned}$$

$$V_{CM_{\max}} = V_t + V_D = 0.5 + 0.5 = +1.0 \text{ V}$$

Since the currents I_{D1} and I_{D2} are still 0.2 mA each,

$$V_{GS} = 0.82 \text{ V}$$

$$\begin{aligned} \text{So, } V_{CM_{\min}} &= V_{SS} + V_{CS} + V_{GS} \\ &= -1.5 \text{ V} + 0.4 \text{ V} + 0.82 \text{ V} = -0.28 \text{ V} \end{aligned}$$

So, the common-mode range is

$$-0.28 \text{ V to } 1.0 \text{ V}$$

Homework #4

3. For the amplifier of Problem 1,

- (a) Find the value of v_{id} that causes Q_1 to conduct the entire current I , and the corresponding values of V_{D1} and V_{D2} .
- (b) Find the value of v_{id} that causes Q_2 to conduct the entire current I , and the corresponding values of V_{D1} and V_{D2} .
- (c) Find the corresponding range of the differential output voltage ($V_{D2} - V_{D1}$).

(a) The value of v_{id} that causes Q_1 to conduct the entire current is $\sqrt{2} V_{OV}$

$$\rightarrow \sqrt{2} \times 0.316 = 0.45 \text{ V}$$

then, $V_{D1} = V_{DD} - I \times R_D$

$$= 1.5 - 0.4 \times 2.5 = 0.5 \text{ V}$$

$$V_{D2} = V_{DD} = +1.5 \text{ V}$$

(b) For Q_2 to conduct the entire current:

$$v_{id} = -\sqrt{2} V_{OV} = -0.45 \text{ V}$$

then,

$$V_{D1} = V_{DD} = +1.5 \text{ V}$$

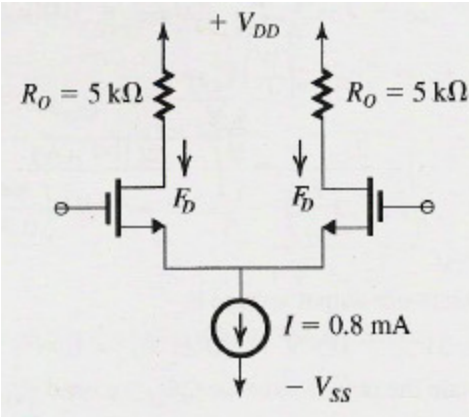
$$V_{D2} = 1.5 - 0.4 \times 2.5 = 0.5 \text{ V}$$

(c) Thus the differential output range is:

$$V_{D2} - V_{D1}: \text{ from } 1.5 - 0.5 = +1 \text{ V}$$

$$\text{to } 0.5 - 1.5 = -1 \text{ V}$$

4. A MOS differential amplifier is operated at a total current of 0.8mA, using transistors with a W/L ratio of 100, $k_n' = \mu_n C_{ox} = 0.2 \text{ mA/V}^2$, $V_A = 20 \text{ V}$, and $R_D = 5 \text{ k}\Omega$. Find $V_{OV} = (V_{GS} - V_t)$, g_m , r_o , and A_d .



$$I_D = \frac{I}{2} = \frac{0.8 \text{ mA}}{2} = 0.4 \text{ mA}$$

$$I_D = \frac{1}{2} k_n' \left(\frac{W}{L} \right) (V_{OV})^2 \text{ So that}$$

$$V_{OV} = \sqrt{\frac{2 I_D}{k_n' \left(\frac{W}{L} \right)}} = \sqrt{\frac{2(0.4 \text{ mA})}{0.2(\text{mA/V}^2)(100)}} = 0.2 \text{ V}$$

$$g_m = \frac{I_D}{V_{OV}/2} = \frac{0.4 \text{ mA}(2)}{0.2 \text{ V}} = 4 \text{ mA/V}$$

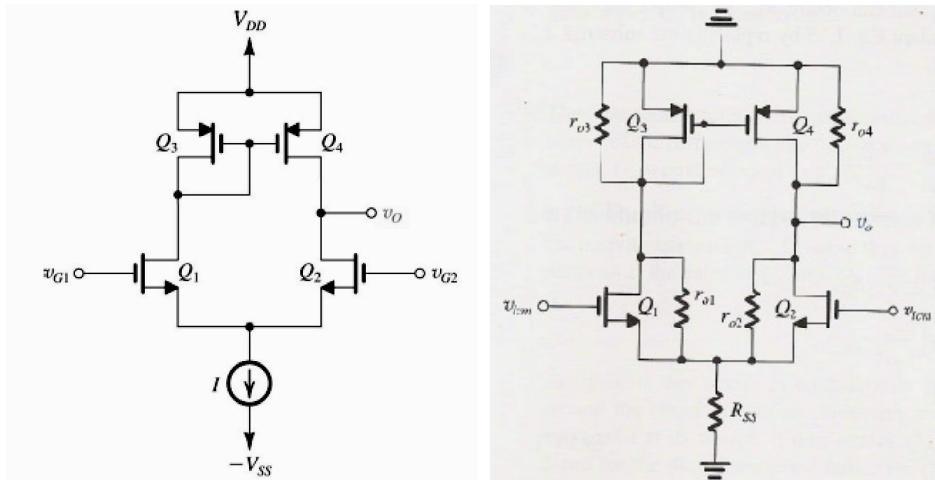
$$r_o = \frac{V_A}{I_D} = \frac{20 \text{ V}}{0.4 \text{ mA}} = 50 \text{ k}\Omega$$

$$A_d = g_m (R_D \parallel r_o)$$

$$A_D = (4 \text{ mA/V})(5 \text{ K} \parallel 50 \text{ K}) = 18.2 \text{ V/V}$$

Homework #4

5. Prove that $A_{cm} \cong -\frac{r_{o4}}{2R_{SS}} \frac{1}{(1+g_{m3}r_{o3})} \cong -\frac{1}{2g_{m3}R_{SS}}$ for the active-loaded MOS differential amplifier below.



$$v_s = v_{icm} \frac{(2R_{SS} \parallel r_{o1})}{(2R_{SS} \parallel r_{o1}) + (1/g_{m1})}$$

$$\cong v_{icm}$$

The short-circuit drain current i_o can be seen to be equal to the current through $2R_{SS}$; thus,

$$i_o = \frac{v_{icm}}{2R_{SS}}$$

which leads to

$$G_{mcm} \cong \frac{i_o}{v_{icm}} = \frac{1}{2R_{SS}}$$

$$R_{o1} = 2R_{SS} + r_{o1} + (g_{m1}r_{o1})(2R_{SS})$$

Similar results can be obtained for Q_2 , namely, the same G_{mcm} and an output resistance R_{o2} given by

$$R_{o2} = 2R_{SS} + r_{o2} + (g_{m2}r_{o2})(2R_{SS})$$

the voltage v_{g3} can be obtained by multiplying $G_{mcm}v_{icm}$ by the total resistance between the d_1 node and ground,

$$v_{g3} = -G_{mcm}v_{icm} \left(R_{o1} \parallel r_{o3} \parallel \frac{1}{g_{m3}} \right)$$

Homework #4

This voltage in turn determines the current i_4 as

$$i_4 = g_{m4}v_{gs3} = g_{m4}v_{g3}$$

Thus,

$$i_4 = -g_{m4}G_{mcm}v_{icm}\left(R_{o1} \parallel r_{o3} \parallel \frac{1}{g_{m3}}\right)$$

Finally, we can obtain the output voltage v_o by writing for the output node,

$$G_{mcm}v_{icm} + i_4 + \frac{v_o}{R_{o2}} + \frac{v_o}{r_{o4}} = 0$$

$$v_o = -v_{icm} \frac{r_{o4} \parallel R_{o2}}{2R_{SS}} \left[1 - g_{m4} \left(R_{o1} \parallel r_{o3} \parallel \frac{1}{g_{m3}} \right) \right]$$

Since $R_{o2} \gg r_{o4}$ and $R_{o1} \gg r_{o3}$, we can neglect both. Also, substituting $g_{m4} = g_{m3}$, we obtain the following expression for A_{cm} ,

$$A_{cm} \equiv \frac{v_o}{v_{icm}} \approx -\frac{r_{o4}}{2R_{SS}} \frac{1}{1 + g_{m3}r_{o3}} \quad \text{if } g_{m3}r_{o3} \gg 1 \text{ and } r_{o3} = r_{o4} \text{ then, } A_{cm} \approx -\frac{1}{2g_{m3}R_{SS}}$$

6. An active-loaded MOS differential amplifier as shown in Problem 5 is specified as follows: $(W/L)_n=200$, $(W/L)_p=200$, $k_n'=\mu_n C_{ox}=2k_p' = 2\mu_p C_{ox}=0.2\text{mA/V}^2$, $|V_A|=20\text{V}$, $I=0.8\text{mA}$, and $R_{SS}=25\text{k}\Omega$. Calculate G_m , R_{out} , A_d , $|A_{cm}|$.

$$(W/L)_n \times \mu_n C_{ox} = 0.2 \text{ m} \times 100 = 20 \text{ m} \frac{\text{A}}{\text{V}}$$

$$(W/L)_p \times \mu_p C_{ox} = 0.1 \text{ m} \times 200 = 20 \text{ m} \frac{\text{A}}{\text{V}}$$

Since all transistors have the same drain current ($I/2$) and the same product $W/L \times \mu C_{ox}$ then all transconductances g_m are identical.

$$|V_{OV}| = \sqrt{\frac{I_D}{20 \text{ mA/V}}} = \sqrt{\frac{0.8 \text{ mA}}{20 \text{ mA/V}}} = 0.2 \text{ V}$$

thus,

$$g_m = \frac{I_D}{V_{OV}} = \frac{(0.8 \text{ mA}/2)}{0.2 \text{ V}} = 4 \text{ m} \frac{\text{A}}{\text{V}}$$

$$G_m = g_m = 4 \text{ mA/V}$$

$$R_O = r_{O2} \parallel r_{O4}$$

$$r_{O2} = \frac{V_{An}}{I_{D2}} = \frac{20}{(0.8 \text{ mA}/2)} = 50 \text{ k}\Omega$$

$$r_{O4} = \frac{V_{Ap}}{I_{D4}} = \frac{20}{(0.8 \text{ mA}/2)} = 50 \text{ k}\Omega$$

thus,

$$R_O = 50 \parallel 50 = 25 \text{ k}\Omega$$

$$A_d = G_m R_O = 4 \frac{\text{mA}}{\text{V}} \times 25 \text{ k}\Omega = 100 \frac{\text{V}}{\text{V}}$$

$$A_{cm} \approx \frac{1}{2g_{m3}R_{SS}} = \frac{1}{2 \times 4 \times 25} = 0.005 \text{ V/V}$$

$$CMRR = \frac{|A_d|}{|A_{cm}|} = \frac{100}{0.005} = 20,000 \rightarrow 86 \text{ dB}$$

7. Design a MOS differential amplifier to operate from $\pm 1\text{V}$ supplies and dissipate no more than 2mW in its equilibrium state. Select the value of $V_{ov}=(V_{GS}-V_t)$ so that the value of v_{id} that steers the current from one side of the pair to the other is 0.4V . The differential voltage gain A_d is to be 5 V/V . Assume $k_n'=400\mu\text{A/V}^2$ and neglect the Early effect. Specify the required values of I , R_D , and W/L .

$$I=2\text{mW}/(1\text{V}-(-1\text{V}))=1\text{mA}$$

$$0.4\text{V}=\sqrt{2}V_{ov}$$

$$V_{ov}=0.2828\text{V}$$

$$R_D=Ad(V_{ov}/I)=5(.2828\text{V}/1\text{mA})=1,414\Omega$$

Homework #4

$$(W/L) = I / (k_n' V_{ov}^2) = 1 \text{ mA} / (400 \times 10^{-6} \cdot 0.2828^2) \approx 32$$

8. In an active-loaded differential amplifier of the form shown in Problem 5, all transistors are characterized by $k_n'(W/L) = 3.2 \text{ mA/V}^2$ and $|V_A| = 20 \text{ V}$. Find the bias current I for which the gain $v_o/v_{id} = 100 \text{ V/V}$.

Each transistor has $I_D = \frac{I}{2}$

$$r_{o2} = r_{o4} = r_o = \frac{|V_A|}{I_D}$$

$$A_d = \frac{1}{2} g_m r_o$$

Since $g_m = \frac{I_D}{V_{OV}/2}$,

$$A_d = \frac{1}{2} \left(\frac{2I_D}{V_{OV}} \right) \cdot \frac{|V_A|}{I_D} = \frac{|V_A|}{V_{OV}}$$

substituting, we

find that

$$V_{OV} = \frac{|V_A|}{A_d} = \frac{20 \text{ V}}{100 \text{ V/V}} = 0.2 \text{ V}$$

$$I = 2I_D = (2) \frac{1}{2} k_n' (W/L) V_{ov}^2$$

$$I = 3.2 \text{ mA/V}^2 (0.2 \text{ V})^2 = 128 \text{ } \mu\text{A}$$

9. It is required to design the active-loaded differential amplifier shown in Problem 5 to obtain a differential gain of 50 V/V. The technology available provides $\mu_n C_{ox} = 4\mu_p C_{ox} = 400 \text{ } \mu\text{A/V}^2$, $|V_A| = 10$, $L = 0.5 \text{ } \mu\text{m}$, $|V_t| = 0.5 \text{ V}$, and operates from $\pm 1 \text{ V}$ supplies. Use a bias current $I = 200 \text{ } \mu\text{A}$ and operate all devices at $|V_{GS} - V_t| = 0.2 \text{ V}$.

- Find the W/L ratios of the four transistors.
- If $V_{CM} = 0$, what is the allowable range of v_o ?
- If I is delivered by a simple NMOS current source operated at the same $V_{GS} - V_t$ and having the same channel length as the other four transistors, determine the CMRR obtained.

$$(a) I_{D1} = I_{D2} = I_{D3} = I_{D4} = I/2 = \frac{200 \text{ } \mu\text{A}}{2} = 100 \text{ } \mu\text{A} = \frac{1}{2} \mu_n C_{ox} \left(\frac{W}{L} \right) V_{OV}^2$$

$$\left(\frac{W}{L} \right)_{1-2} = \frac{2I_D}{\mu_n C_{ox} V_{OV}^2} = \frac{2(100 \text{ } \mu\text{A})}{400 \text{ } \mu\text{A/V} (0.2 \text{ V})^2} = 12.5$$

For Q_3 and Q_4 ,

$$\left(\frac{W}{L} \right)_{3-4} = \frac{2I_D}{\mu_p C_{ox} V_{OV}^2} = \frac{2(100 \text{ } \mu\text{A})}{100 \text{ } \mu\text{A/V}^2 (0.2 \text{ V})^2} = 50$$

(b) $V_{omax} = V_{G4} + |V_t| = V_{DD} - |V_{GS}| + |V_t| = 1 - 0.2 = 0.8 \text{ V}$

$V_{omin} = V_{G2} - V_t = 0 - 0.5 = -0.5 \text{ V}$

Range is -0.5 to 0.8 V

(c) Q_5 delivers $I = 200 \text{ } \mu\text{A}$, and $L = 0.5 \text{ } \mu\text{m}$,

$V_{ov} = 0.2 \text{ V}$. So,

$$r_{O5} = \frac{|V_A'|}{I} \cdot L = \frac{(20 \text{ V}/\mu\text{m})(0.5 \mu\text{m})}{0.2 \text{ mA}} = 50 \text{ k}\Omega$$

$$r_{O5} = r_{O4} = r_o = 100 \text{ k}\Omega$$

$$A_{cm} = \frac{v_o}{v_{icm}} \approx -\frac{r_{O4}}{2R_{SS}} \cdot \frac{1}{1 + g_{m3} r_{O3}} = -\frac{100 \text{ k}}{2(50 \text{ k})} \cdot \frac{1}{1 + (1 \text{ mA/V})(100 \text{ k})} = -0.01$$

$$CMRR(\text{dB}) = 20 \log_{10} \frac{|A_d|}{|A_{cm}|} = 20 \log_{10} \left(\frac{50}{0.01} \right) = 74 \text{ dB}$$